

SANYO	No.1425C	2SA1380/2SC3502
		PNP/NPN Epitaxial Planar Silicon Transistors Ultrahigh-Definition CRT Display Video Output Applications

Features

- High breakdown voltage : $V_{CEO} \geq 200V$.
- Small reverse transfer capacitance and excellent high-frequency characteristics :
 $C_{re} = 1.2pF(NPN), 1.7pF(PNP) V_{CB} = 30V$.
- Adoption of FBET process.

() : 2SA1380

Absolute Maximum Ratings at $T_a = 25^\circ C$

Collector-to-Base Voltage	V_{CBO}	(-)200	unit
Collector-to-Emitter Voltage	V_{CEO}	(-)200	V
Emitter-to-Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)100	mA
Collector Current (Pulse)	I_{CP}	(-)200	mA
Collector Dissipation	P_C	1.2	W
		5	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

$T_c = 25^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

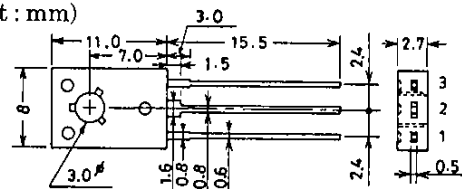
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)150V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = (-)10V, I_C = (-)10mA$	40*		320*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)30V, I_C = (-)10mA$		150		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-)30V, f = 1MHz$		1.7		pF
				(2.6)		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB} = (-)30V, f = 1MHz$		1.2		pF
				(1.7)		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)200			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)200			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V

* : The 2SA1380/2SC3502 are classified by 10mA h_{FE} as follows :

40 C 80	60 D 120	100 E 200	160 F 320
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Package Dimensions 2009B

(unit : mm)



JEDEC: TO-126

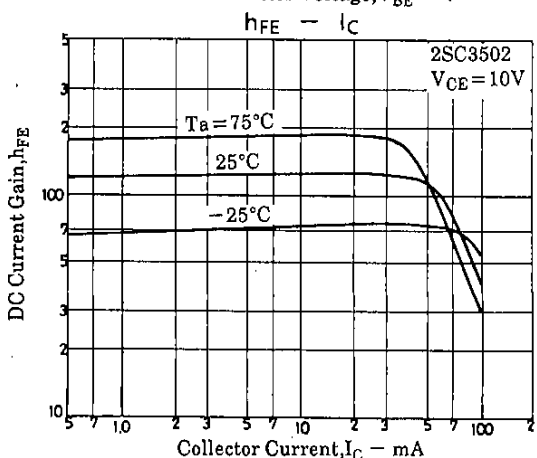
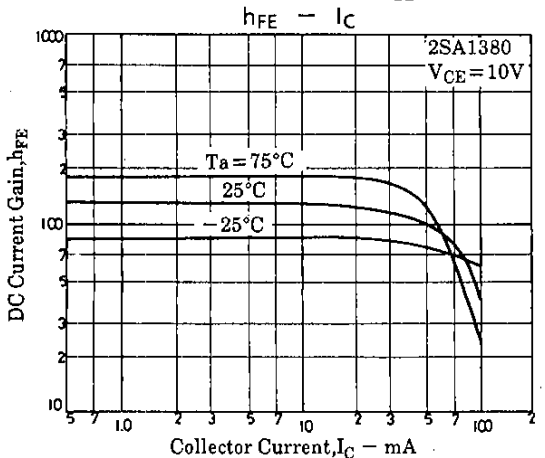
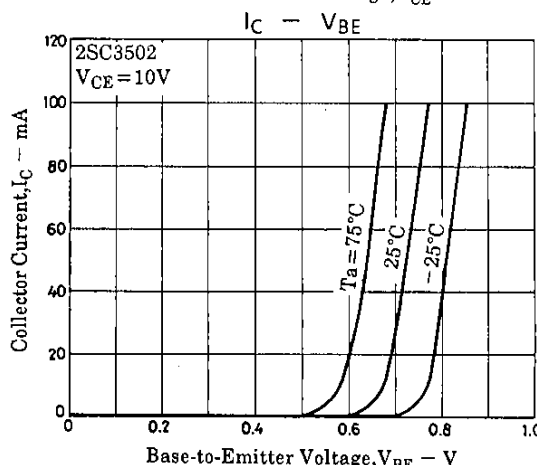
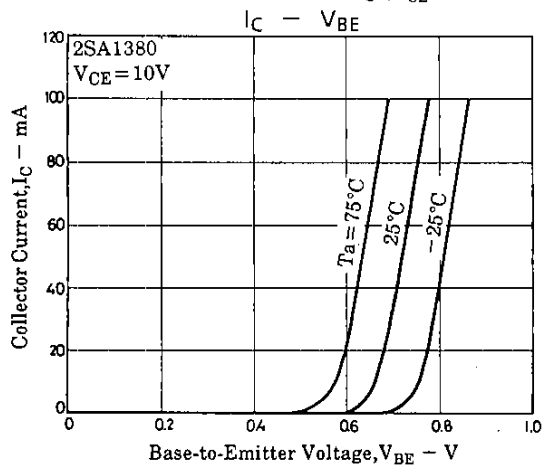
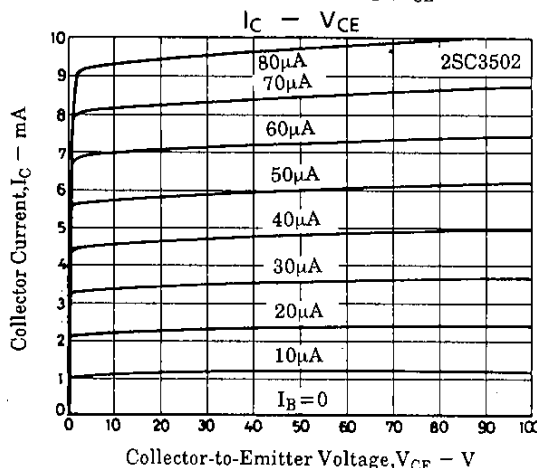
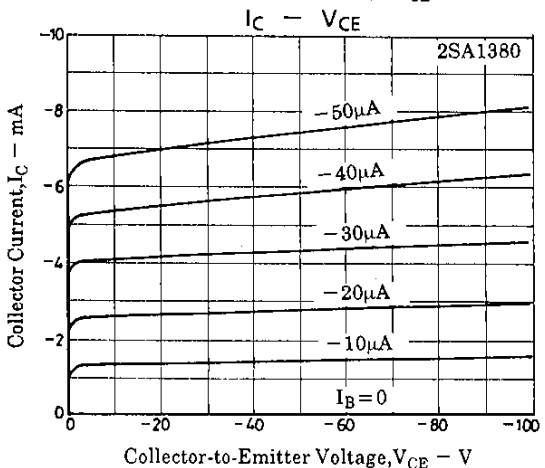
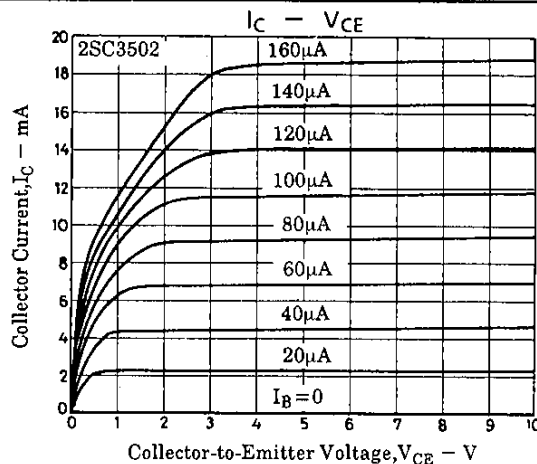
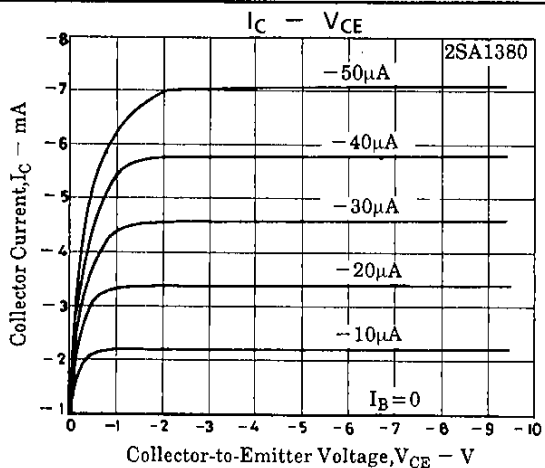
- 1 : Emitter
- 2 : Collector
- 3 : Base

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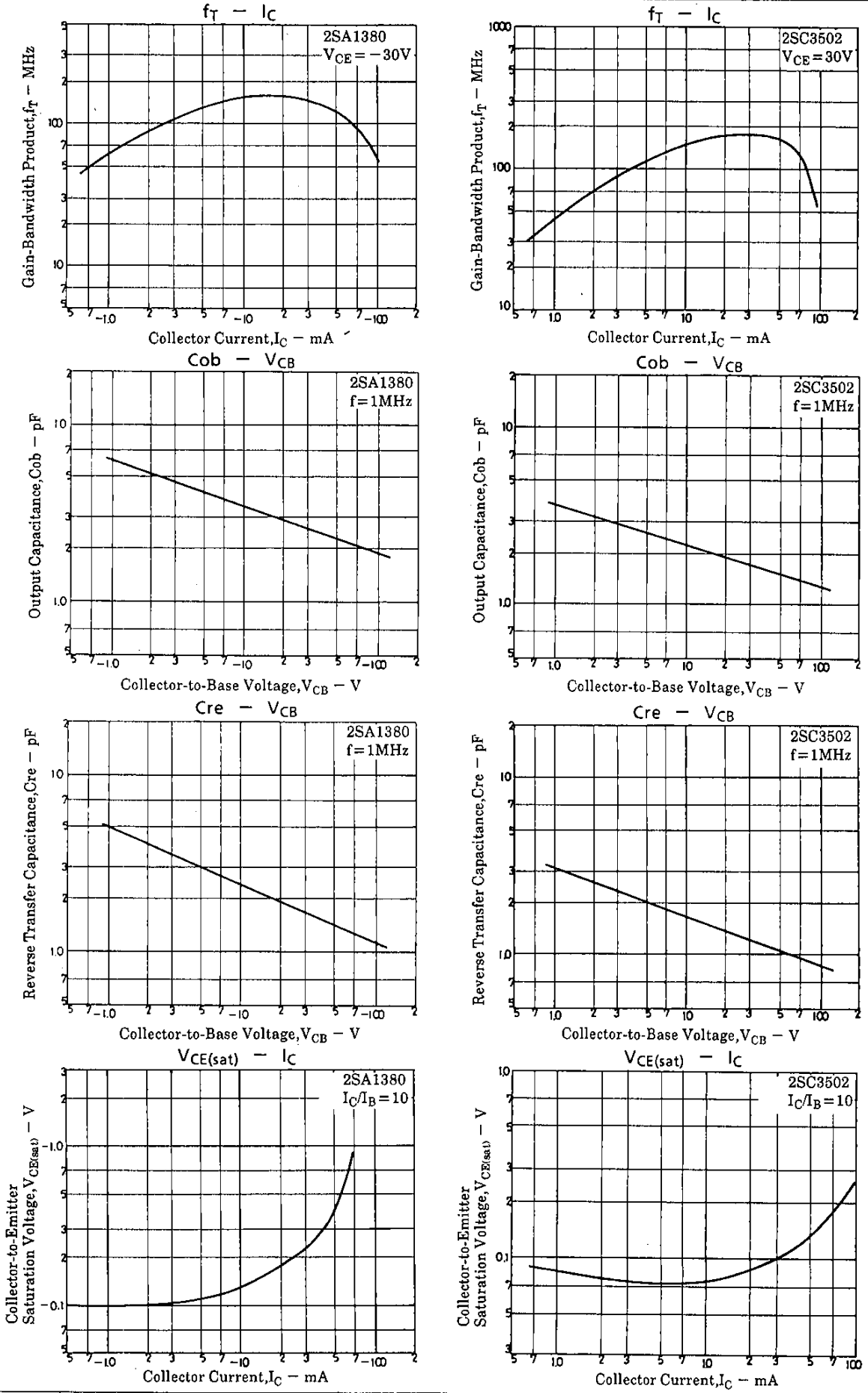
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

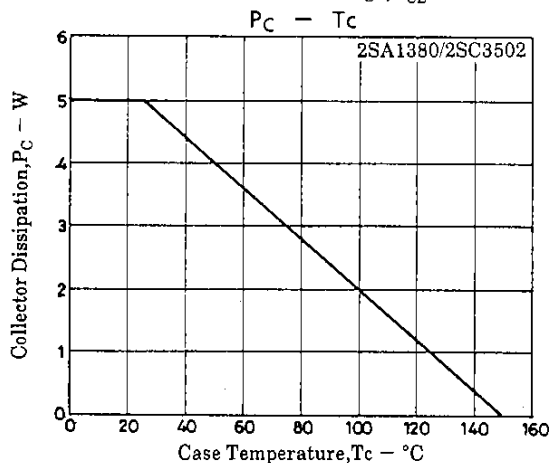
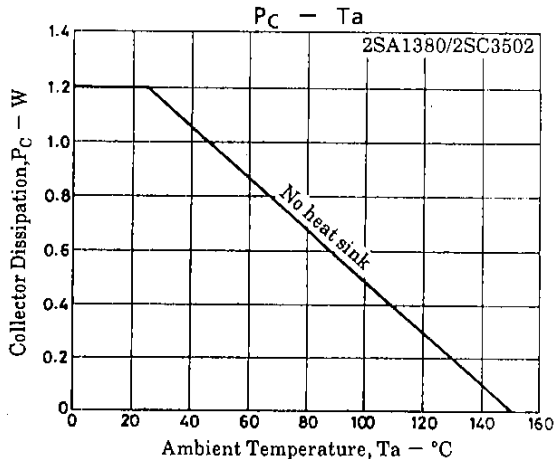
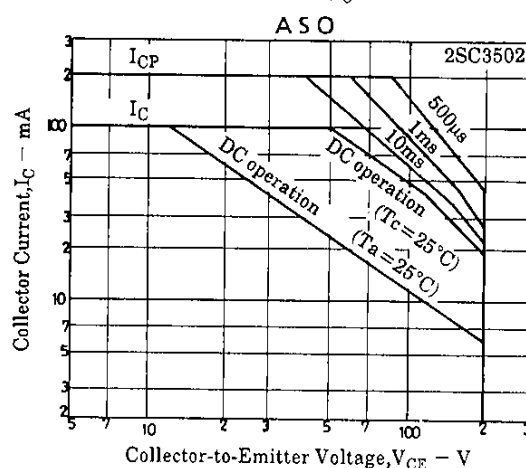
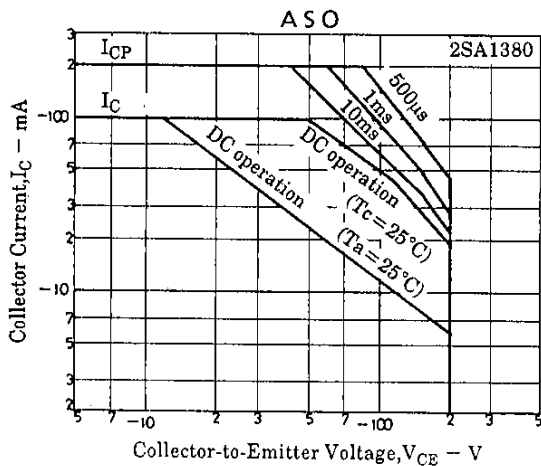
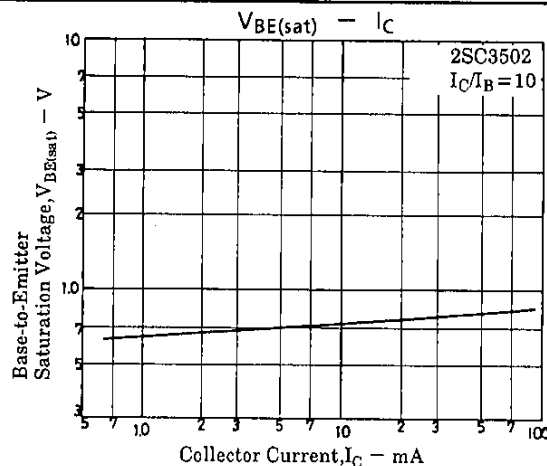
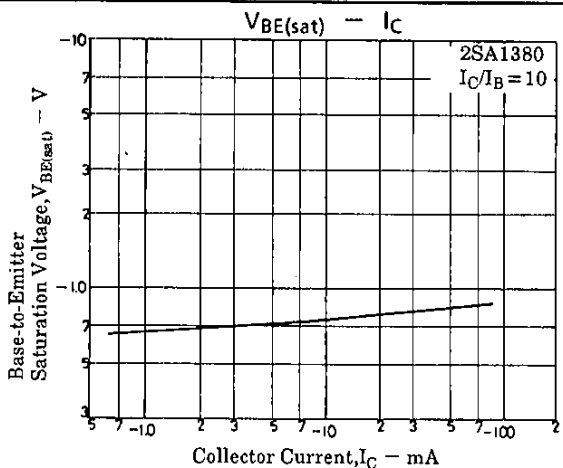
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2SA1380/2SC3502



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